



CS37N06 AQ4-G

General Description:

CS37N06 AQ4-G, the silicon N-channel Enhanced VDMOSFETs, is obtained by the high density Trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This device is suitable for use as a load switch and PWM applications. The package form is PDFN 3.3*3.3

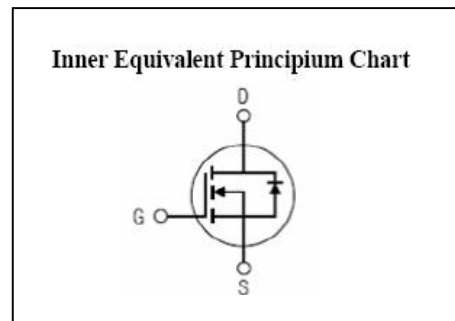
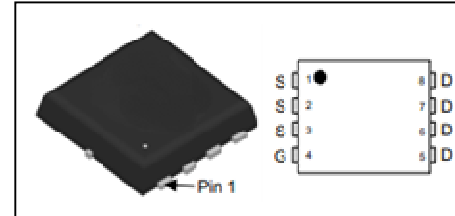
Features:

- I Fast Switching
- I Low ON Resistance($R_{DS(ON)} \leq 17 \text{ m}\Omega$)
- I Low Gate Charge
- I Low Reverse transfer capacitances
- I 100% Single Pulse avalanche energy Test
- I Halogen Free

Applications:

Power switch circuit of adaptor and charger.

| | | |
|-----------------|------|------------------|
| V_{DSS} | 65 | V |
| I_D | 37 | A |
| P_D | 41.6 | W |
| $R_{DS(ON)Typ}$ | 14 | $\text{m}\Omega$ |



Absolute (T_J= 25 °C unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|----------------|---|-----------------|-------|
| V_{DSS} | Drain-to-Source Voltage | 65 | V |
| I_D | Continuous Drain Current $T_C = 25 \text{ }^\circ\text{C}$ | 37 | A |
| | Continuous Drain Current $T_C = 100 \text{ }^\circ\text{C}$ | 23.3 | A |
| I_{DM}^{a1} | Pulsed Drain Current $T_C = 25 \text{ }^\circ\text{C}$ | 148 | A |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS}^{a2} | Avalanche Energy | 114.5 | mJ |
| P_D | Power Dissipation $T_C = 25 \text{ }^\circ\text{C}$ | 41.6 | W |
| | Derating Factor above 25 °C | 0.33 | W/°C |
| T_J, T_{stg} | Operating Junction and Storage Temperature Range | 150, -55 to 150 | °C |

Electrical Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified):

| OFF Characteristics | | | | | | |
|----------------------------|-----------------------------------|--|--------|------|------|---------|
| Symbol | Parameter | Test Conditions | Rating | | | Units |
| | | | Min. | Typ. | Max. | |
| V_{DSS} | Drain to Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$ | 65 | -- | -- | V |
| I_{DSS} | Drain to Source Leakage Current | $V_{DS}=65V, V_{GS}=0V, T_j=25^\circ\text{C}$ | -- | -- | 1 | μA |
| | | $V_{DS}=52V, V_{GS}=0V, T_j=125^\circ\text{C}$ | -- | -- | 100 | |
| $I_{GSS(F)}$ | Gate to Source Forward Leakage | $V_{GS}=20V$ | -- | -- | 100 | nA |
| $I_{GSS(R)}$ | Gate to Source Reverse Leakage | $V_{GS}=-20V$ | -- | -- | -100 | nA |

| ON Characteristics | | | | | | |
|--|-------------------------------|-------------------------------|--------|------|------|-----------|
| Symbol | Parameter | Test Conditions | Rating | | | Units |
| | | | Min. | Typ. | Max. | |
| $R_{DS(ON)}$ | Drain-to-Source On-Resistance | $V_{GS}=10V, I_D=10A$ | -- | 14 | 17 | $m\Omega$ |
| | | $V_{GS}=4.5V, I_D=6A$ | -- | 18 | 22 | $m\Omega$ |
| $V_{GS(TH)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1.0 | 1.65 | 2.5 | V |
| Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$ | | | | | | |

| Dynamic Characteristics | | | | | | |
|--------------------------------|------------------------------|--|--------|------|------|----------|
| Symbol | Parameter | Test Conditions | Rating | | | Units |
| | | | Min. | Typ. | Max. | |
| R_g | Gate resistance | $V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$ | -- | 2.3 | -- | Ω |
| C_{iss} | Input Capacitance | $V_{GS}=0V, V_{DS}=30V, f=1.0\text{MHz}$ | -- | 1668 | -- | pF |
| C_{oss} | Output Capacitance | | -- | 113 | -- | |
| C_{rss} | Reverse Transfer Capacitance | | -- | 86 | -- | |

| Resistive Switching Characteristics | | | | | | |
|--|---------------------------------|--|--------|------|------|-------|
| Symbol | Parameter | Test Conditions | Rating | | | Units |
| | | | Min. | Typ. | Max. | |
| $t_{d(ON)}$ | Turn-on Delay Time | $V_{GS}=10V, R_G=3\Omega, V_{DD}=30V, I_D=30A$ | -- | 10.6 | -- | ns |
| t_r | Rise Time | | -- | 40.8 | -- | |
| $t_{d(OFF)}$ | Turn-Off Delay Time | | -- | 5.6 | -- | |
| t_f | Fall Time | | -- | 6.8 | -- | |
| Q_g | Total Gate Charge | $I_D=30A, V_{DD}=30V, V_{GS}=10V$ | -- | 33.8 | -- | nC |
| Q_{gs} | Gate to Source Charge | | -- | 5.9 | -- | |
| Q_{gd} | Gate to Drain ("Miller") Charge | | -- | 9.4 | -- | |

| Source-Drain Diode Characteristics | | | | | | |
|---|--|------------------------------------|--------|------|------|-------|
| Symbol | Parameter | Test Conditions | Rating | | | Units |
| | | | Min. | Typ. | Max. | |
| I_S | Continuous Source Current (Body Diode) | $T_C = 25\text{ }^\circ\text{C}$ | -- | -- | 37 | A |
| I_{SM} | Maximum Pulsed Current (Body Diode) | | -- | -- | 148 | A |
| V_{SD} | Diode Forward Voltage | $I_S=10\text{A}, V_{GS}=0\text{V}$ | -- | -- | 1.2 | V |
| t_{rr} | Reverse Recovery Time | $di/dt=100\text{A}/\mu\text{s}$ | -- | 31.6 | -- | ns |
| Q_{rr} | Reverse Recovery Charge | $I_F=30\text{A}$ | -- | 49.5 | -- | nC |
| Pulse width $t_p \leq 300\mu\text{s}$, $\delta \leq 2\%$ | | | | | | |

| Symbol | Parameter | Max. | Units |
|-----------------|---------------------|------|---------------------------|
| $R_{\theta JC}$ | Junction-to-Case | 3 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Junction-to-Ambient | 75 | $^\circ\text{C}/\text{W}$ |

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=0.5\text{mH}, I_{as}=21.4\text{A}$ Start $T_J=25^\circ\text{C}$

^{a3}: Recommend soldering temperature defined by IPC/JEDEC J-STD 020

Characteristics Curve:

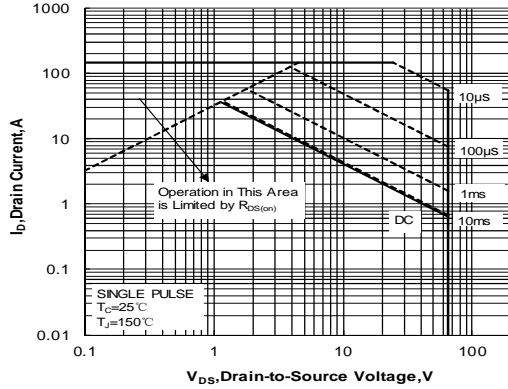


Figure 1 . Maximum Safe Operating Area

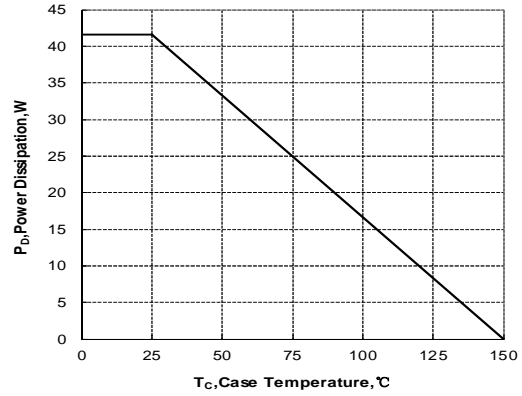


Figure 2. Maximum Power Dissipation vs Case Temperature

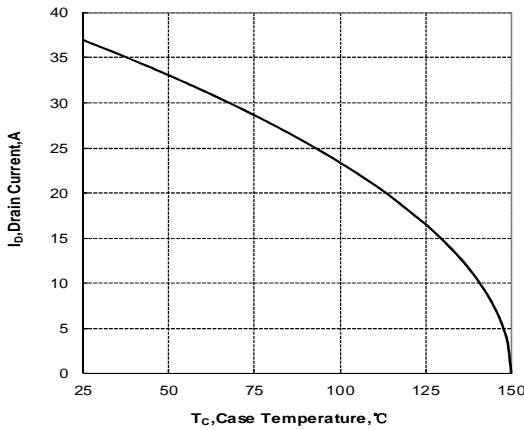


Figure 3. Maximum Continuous Drain Current vs Case Temperature

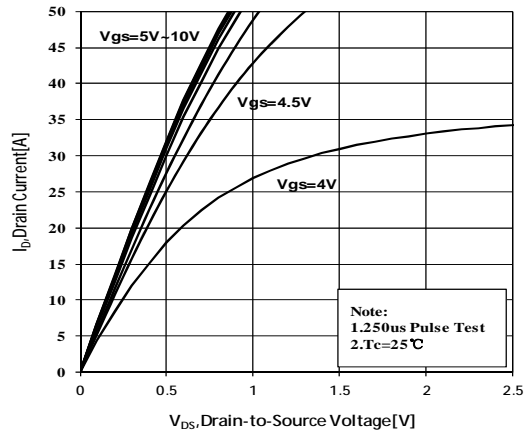


Figure 4. Typical output Characteristics

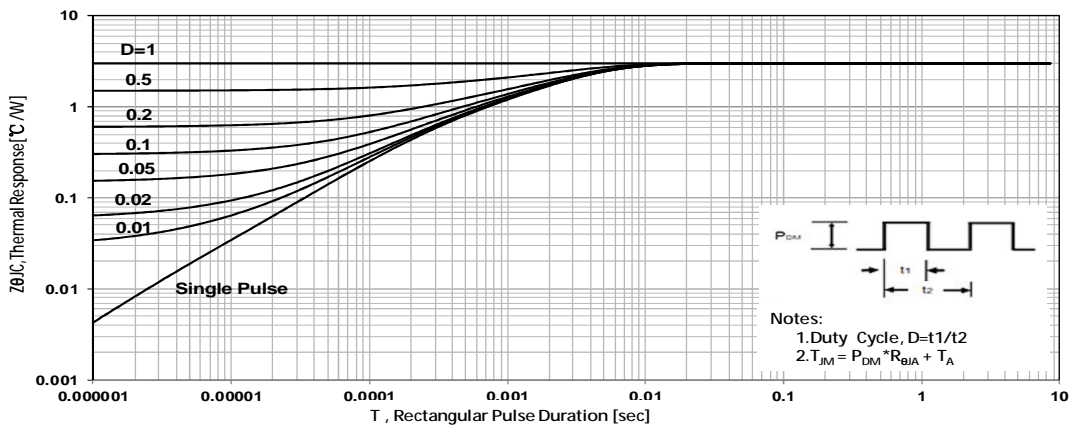


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

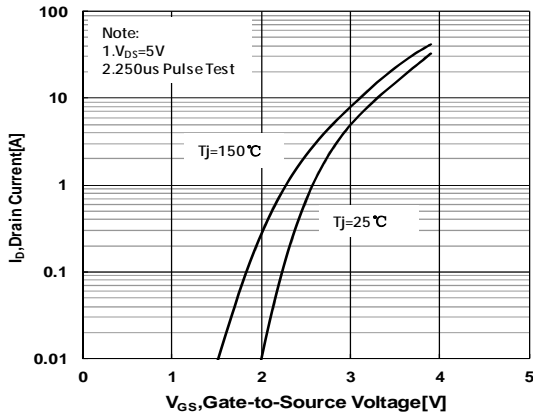


Figure 6 Typical Transfer Characteristics

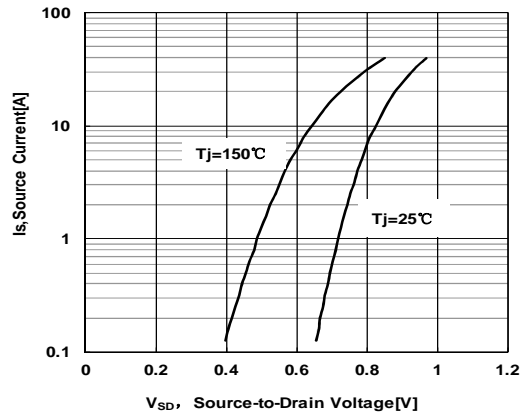


Figure 7 Typical Body Diode Transfer Characteristics

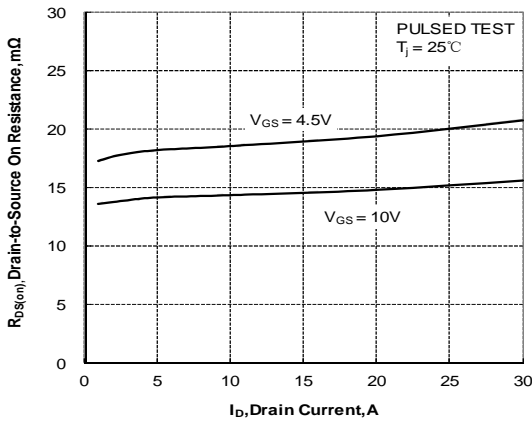


Figure 8. Drain-to-Source On Resistance vs Drain Current

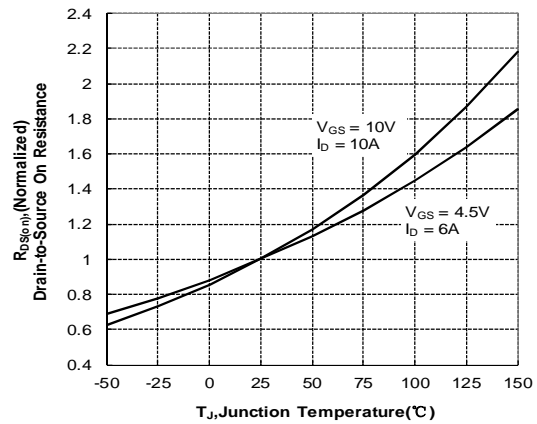


Figure 9. Normalized On Resistance vs Junction Temperature

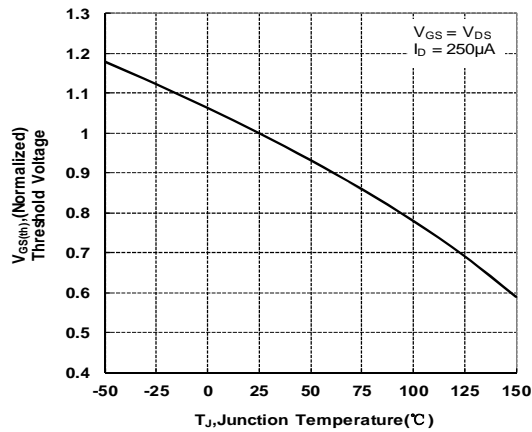


Figure 10. Normalized Threshold Voltage vs Junction Temperature

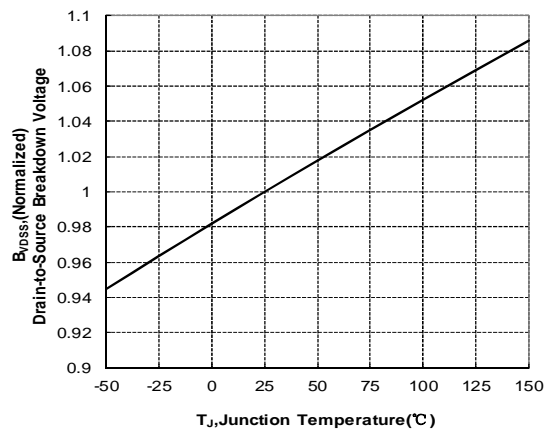


Figure 11. Normalized Breakdown Voltage vs Junction Temperature

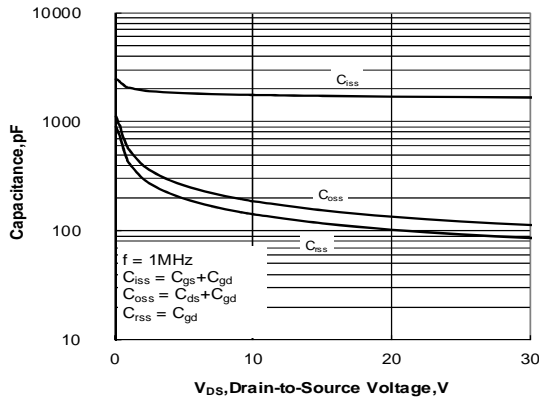


Figure 12. Capacitance Characteristics

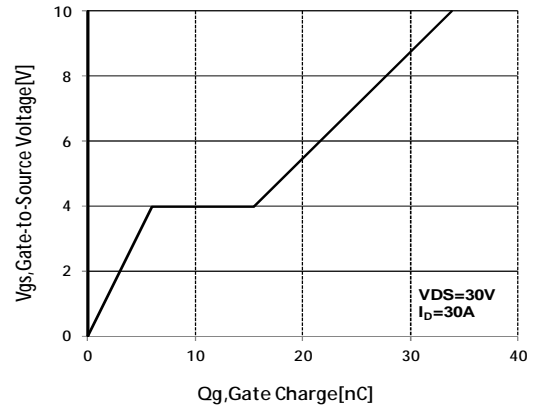


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform



Figure 14. Gate Charge Test Circuit



Figure 15. Gate Charge Waveforms



Figure 16. Resistive Switching Test Circuit



Figure 17. Resistive Switching Waveforms



Figure 18. Diode Reverse Recovery Test Circuit



Figure 19. Diode Reverse Recovery Waveform

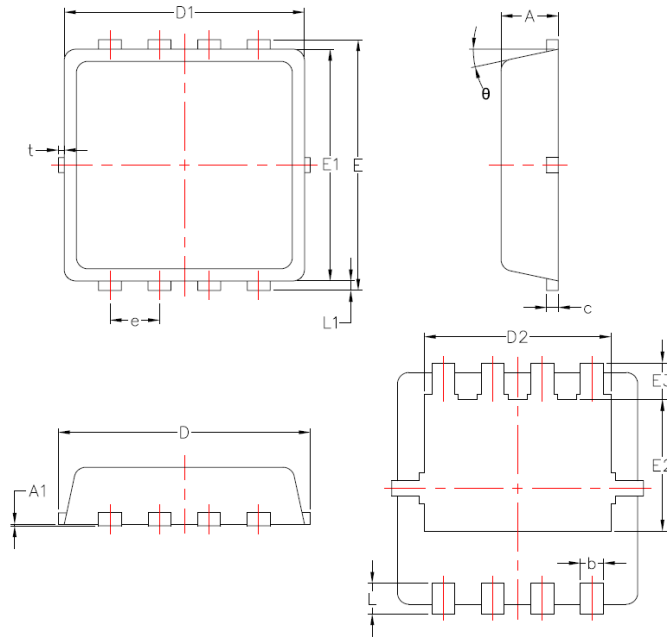


Figure20.Unclamped Inductive Switching Test Circuit



Figure21.Unclamped Inductive Switching Waveform

Package Information:



| Items | Values(mm) | |
|-------|------------|------|
| | MIN | MAX |
| A | 0.7 | 0.9 |
| A1 | / | 0.05 |
| b | 0.2 | 0.4 |
| c | 0.1 | 0.25 |
| D | 3.05 | 3.55 |
| D1 | 2.90 | 3.35 |
| D2 | 2.15 | 2.65 |
| E | 3.05 | 3.55 |
| E1 | 2.80 | 3.30 |
| E2 | 1.54 | 1.94 |
| E3 | 0.18 | 0.65 |
| e | 0.55 | 0.75 |
| L | 0.2 | 0.6 |
| L1 | 0.05 | 0.25 |
| t | / | 0.15 |
| θ | 8° | 14° |

PDFN3.3×3.3Package

The name and content of poisonous and harmful material in products

| Part's Name | Hazardous Substance | | | | | | | | | |
|---------------|---|-------|------------|--------|-------|-------|-------|-------|-------|-------|
| | Pb | Hg | Cd | Cr(VI) | PBB | PBDE | DIBP | DEHP | DBP | BBP |
| Limit | ≤0.1% | ≤0.1% | ≤0.01 % | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% |
| Lead Frame | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ |
| Molding | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ |
| Chip | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ |
| Wire Bonding | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ |
| Electric glue | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ | ○ |
| Note | ○: Means the hazardous material is under the criterion of 2011/65/EU. ×: Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS. | | | | | | | | | |

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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